

- *TTL Compatible (3.3v)*
- *2 Packaging Styles*
- *Ultra Low Jitter*
- *Low Phase Noise*
- *Immediate Delivery*



Part Numbering Example: CAM C 7 L Z - A5 B6 - XXX.XXXX TS

CAM	C	7	L	Z	A5	B6	XXX.XXXX	TS
SERIES	OUTPUT	PACKAGE STYLE	VOLTAGE	PACKAGING OPTIONS	OPERATING TEMP.	STABILITY	FREQUENCY	TRI-STATE
CAM	C=HCMOS	1 = Full Size 4 = Half Size 5 = 5 X 3.2 Ceramic 7 = 5 X 7 Ceramic	L = 3.3 V S = 2.5 V	Blank = Bulk T = Tube Z = Tape and Reel	Blank = 0°C +70°C A5 = -20°C +70°C A7 = -40°C +85°C	B6 = ±100 ppm BP = ±50 ppm BR = ±25 ppm	1.500~200.000 MHz	TS = Tri-State NC = No Connect

Specifications:

Description	Min	Typ	Max	Unit
Frequency Range: Programmable to Any Discrete Frequency	1.500		200.000	MHz
Available Stability Options:	-100 -50 -25		100 50 25	ppm ppm ppm
Supply Voltage Options: (1-133 MHz) (1-200 MHz)	2.25 3.0	2.5 3.3	2.75 3.6	V V
Operating Temperature Range Options:	0 -20 -40		+70 +70 +85	°C °C °C
Storage Temperature:	-55		+125	°C
Aging (PPM/Year) Ta=25C, Vdd=3.3V/2.5V			±5	
Output Level:	HCMOS			
Packaging:	Tape and Reel (1K per Reel) Tube			

Operating Conditions:

Description	Min	Max	Unit
Vdd Supply Voltage	2.25	3.6	V
Vdd Rise Time	100		µS
HCMOS Max Capacitive Load on outputs for CMOS levels Frequency: < 40 MHz Frequency: 40-200 MHz		30 15	pF pF



- *TTL Compatible (3.3v)*
- *2 Packaging Styles*
- *Low Jitter*
- *Low Phase Noise*
- *Immediate Delivery*

Electrical Characteristics

Description	TEST CONDITIONS	Min	Typ	Max	Unit
Input Characteristics (Pin 1): V _{IL} , Low-Level Input Voltage TO DISABLE OUTPUT	3.0–3.6V V _{dd}			0.2V _{dd}	V
V _{IH} , High-Level Input Voltage TO ENABLE OUTPUT OR OPEN	3.0–3.6V V _{dd}	0.7V _{dd}			
I _{IL} , Input Low Current I _{IH} , Input High Current	V _{IN} = 0V V _{IN} = V _{dd}			80 10	μA μA
Output Characteristics: V _{OL} , Low-Level Output Voltage	3.0V–3.6V V _{dd} , 8 mA I _{oL}			0.4	V
V _{OHC} MOS, High-level HCMOS Voltage	2.25V–3.6V V _{dd} , -8 mA I _{oL}	V _{dd} -0.4			V V
Power Supply Current: (unloaded)	2.25–3.6 V _{dd} , OUTPUT FREQ ≤ 200 MHz			35	mA
Tristate Internal Pull-Up Res:	2.25–3.6V V _{dd} , V _{IN} = 0.7V Output active when high	50	70	90	KΩ
Tri-State Leakage Current:	3.6V V _{dd}		20		μA
Output Enable Mode:	Output is Tri-States				

"Tristate internal pull up. Output active when high"

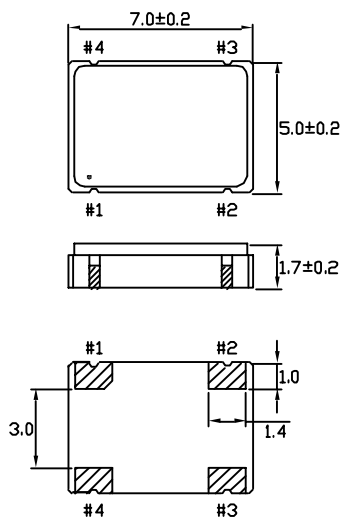
Output Clock Switching Characteristics

Description	TEST CONDITIONS	Min	Typ	Max	Unit
Duty Cycle: HCMOS @ V _{dd} /2	2.25 V – 3.6V V _{dd}	45		55	%
Output Clock Rise/Fall:	0.2–0.8V _{dd} , 2.25–3.6 V _{dd} , C _L = 30 0.2–0.8V _{dd} , 2.25–3.6 V _{dd} , C _L = 15			4.0 2.4	nS nS
Start Up Time:	From power on		3	10	mS
RMS Period Jitter:			10		pS
RMS Integrated Jitter:	12kHz to 20MHz		15		pS
Phase Noise:	@ 10kHz			-100	dBc/Hz



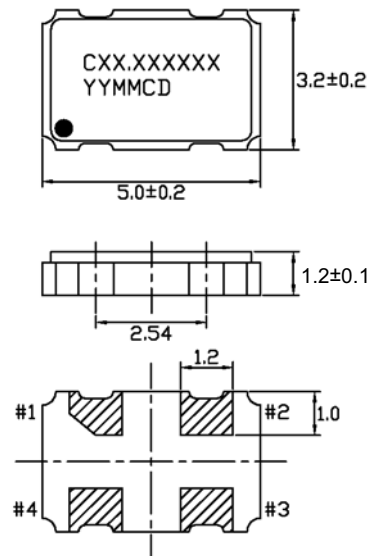
- *TTL Compatible (3.3v)*
- *2 Packaging Styles*
- *Low Jitter*
- *Low Phase Noise*
- *Immediate Delivery*

Style 7 5x7 Ceramic SMD



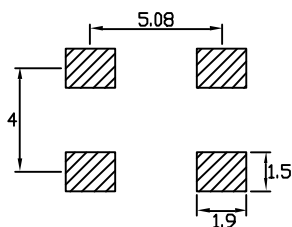
PIN FUNCTION
 1 CONTROL
 2 GND
 3 OUTPUT
 4 Vdd

Style 5 5x3.2 Ceramic SMD

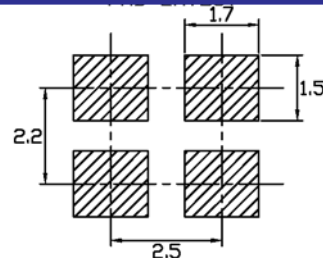


PIN FUNCTION
 1 CONTROL
 2 GND
 3 OUTPUT
 4 Vdd

Recommended Solder Pad Layout



Recommended Solder Pad Layout



Note: Bypass Vdd to GND with a 0.01µF capacitor